

ROITHNER LASERTECHNIK

A-1040 WIEN, FLEISCHMANNGASSE 9

TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43

e-mail: office@roithner-laser.com http://www.roithner-laser.com

RLT80805MG TECHNICAL DATA



Infrared Laserdiode

Structure: **GaAlAs double heterostructure**

Lasing wavelength: **808 nm typ.**

Max. optical power: **5 mW**

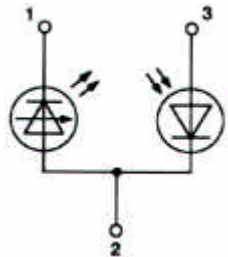
Package: **5.6 mm**

NOTE!

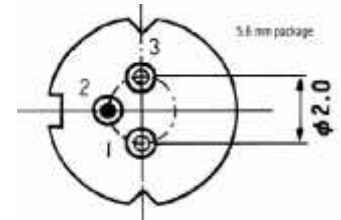
LASERDIODE
MUST BE COOLED!



PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (Tc=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	5	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operating Temperature	T _C	-10 .. +45	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	kink free			5	mW
Threshold Current	I _{th}		20	25	40	mA
Operation Current	I _{op}	P _o = 5 mW		40	50	mA
Operation Voltage	V _{op}	P _o = 5 mW			2.5	V
Lasing Wavelength	λ _p	P _o = 5 mW	790	808	810	nm
Beam Divergence	θ _∥	P _o = 5 mW	5	8	11	°
Beam Divergence	θ _⊥	P _o = 5 mW	25	31	37	°
Astigmatism	A _s	P _o = 5 mW, NA=0.4		5		μm
Monitor Current	I _m	P _o = 5mW, V _r =5V		10		μA